

SPECIFICATION OF LED CHIP

C625-30V

[ORANGE]

1) Commodity Type and Physical Characteristics.

1. Material InGaAlP/GaAs
2. Electrode
 - Top Side P (anode) side : Au Alloy/Al or Au Pad
 - Bottom Side N (cathode) side : Au Alloy
3. Electrode Pattern Fig.1
4. Chip Size Fig.2
5. Chip Thickness Fig.2
6. Emission Area Fig.2

2) Electro-Optical Characteristics

Parameters	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V _f	I _f =20mA		2.0	2.4	V
Reverse Current	I _r	V _r =5V			10	uA
Brightness	I _v	I _f =20mA	50	90		mcd
Power Intensity	P _o	I _f =20mA	0.7	1.3		mW
Peak Wavelength	λ _P	I _f =20mA	615	625	635	nm
Spectral Radiation Bandwidth	Δλ	I _f =20mA		20		nm
RiseTime	t _r	I _f =20mA		100		ns
FallTime	t _f	I _f =20mA		100		ns

‡ Die shall be mounted on TO=18 gold header without resin coated.

[Unit: μm]

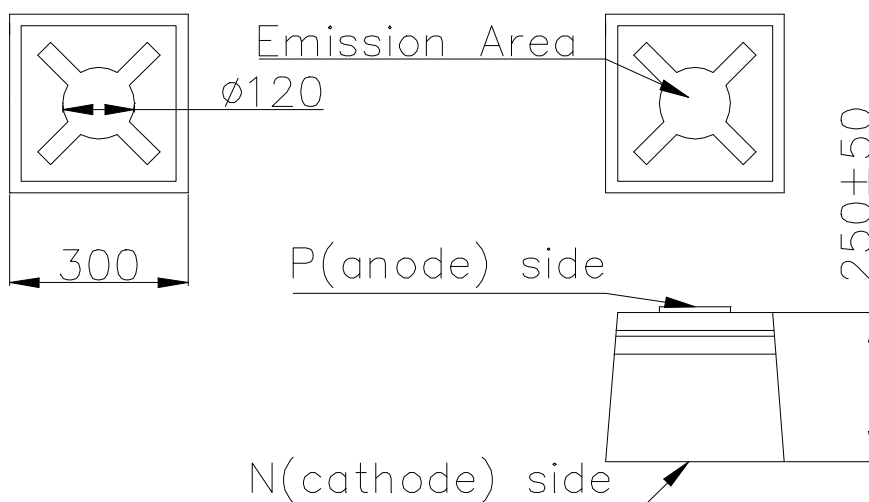


Fig.1 Electrode Pattern

Fig.2 Chip size and Emission Area